SIEMENS

NEW

IL221AT/IL222AT/IL223AT

PHOTODARLINGTON SMALL OUTLINE SURFACE MOUNT OPTOCOUPLER

FEATURES

- **High Current Transfer Ratio, I_F=1 mA, IL221AT, 100% Minimum IL222AT, 200% Minimum IL223AT, 500% Minimum**
- **Withstand Test Voltage, 2500 VAC_{RMS}**
- **Electrical Specifications Similar to Standard 6 Pin Coupler**
- **Industry Standard SOIC-8 Surface Mountable Package**
- **Standard Lead Spacing, .05"**
- **Available in Tape and Reel (suffix T) (Conforms to EIA Standard RS481A)**
- **Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering**
- **Underwriters Lab File #E52744 (Code Letter P)**

DESCRIPTION

The IL221AT/IL222AT/IL223AT is a high current transfer ratio (CTR) optocoupler with a Gallium Arsenide infrared LED emitter and a silicon NPN photodarlington transistor detector.

This device has a CTR tested at an 1 mA LED current. This low drive current permits easy interfacing from CMOS to LSTTL or TTL.

This optocoupler is constructed in a standard SOIC-8 foot print which makes it ideally suited for high density applications. In addition to eliminating through-holes requirements, this package conforms to standards for surface mounted devices.

Maximum Ratings

Emitter

Peak Reverse Voltage ..... 6.0 V
Continuous Forward Current ..... 60 mA
Power Dissipation at 25°C ..... 90 mW
Derate Linearly from 25°C ..... 1.2 mW/°C

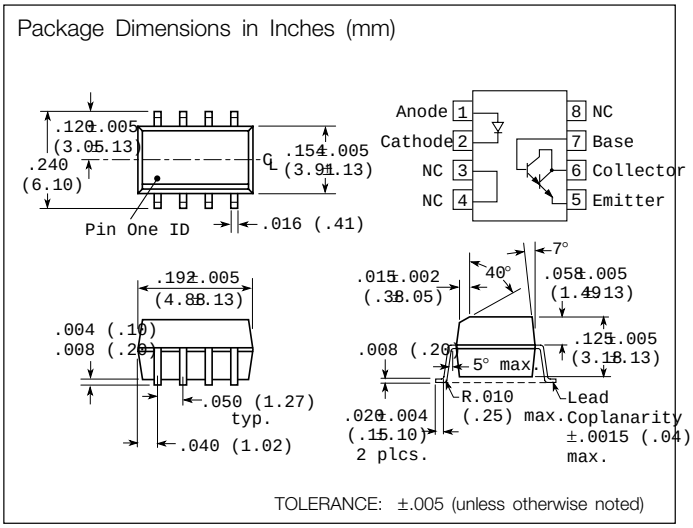
Detector

Collector-Emitter Breakdown Voltage ..... 30 V
Emitter-Collector Breakdown Voltage ..... 5 V
Collector-Base Breakdown Voltage ..... 70 V
Power Dissipation ..... 150 mW
Derate Linearly from 25°C ..... 2.0 mW/°C

Package

Total Package Dissipation at 25°C Ambient (LED + Detector) ..... 240 mW
Derate Linearly from 25°C ..... 3.3 mW/°C
Storage Temperature ..... –55°C to +150°C
Operating Temperature ..... –55°C to +100°C
Soldering Time at 260°C ..... 10 sec.

Package Dimensions in Inches (mm)



TOLERANCE: ±.005 (unless otherwise noted)

Characteristics (T_A=25°C)

	Symbol	Min.	Typ.	Max.	Unit	Condition
Emitter						
Forward Voltage	V_F		1.0	1.5	V	I_F=1mA
Reverse Current	I_R		0.1	100	µA	V_R=6.0 V
Capacitance	C_O		25		pF	V_F=0 V, F=1 MHz
Detector						
Breakdown Voltage						
Collector-Emitter	BV_{CEO}	30			V	I_C=100 µA
Emitter-Collector	BV_{ECO}	5			V	I_E=100 µA
Collector-Base Voltage	BV_{CBO}	70				I_C=10 µA
Collector-Emitter Capacitance	C_{CE}		3.4		pF	V_{CE}=10 V
Package						
DC Current Transfer Ratio	CTR_{DC}					I_F=1 mA, V_{CE}=5 V
IL221AT		100				
IL222AT		200				
IL223AT		500				
Collector-Emitter Saturation Voltage	$V_{CE\,sat}$			1	V	I_{CE}=0.5 mA, I_F=1 mA
Isolation Test Voltage	V_{IO}	2500			VAC_{RMS}	t=1 sec.
Capacitance, Input to Output	C_{IO}		0.5		pF	
Resistance, Input to Output	R_{IO}		100		GΩ	

Specifications subject to change.

Figure 1. Forward voltage versus forward current

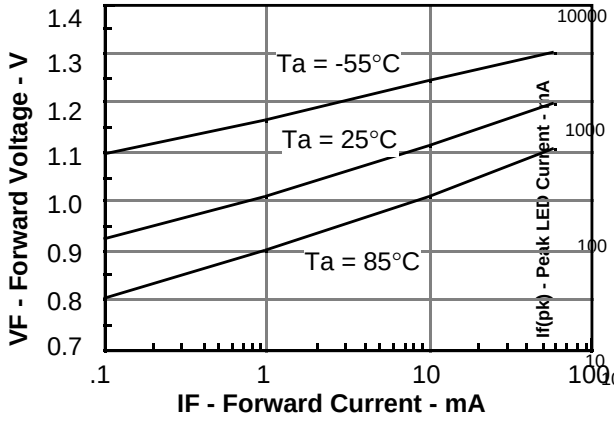


Figure 2. Peak LED current versus duty factor, Tau

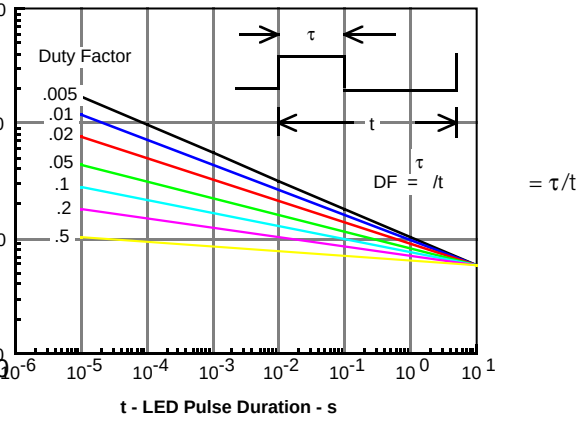


Figure 3. Normalized CTR_{CB} versus I_F

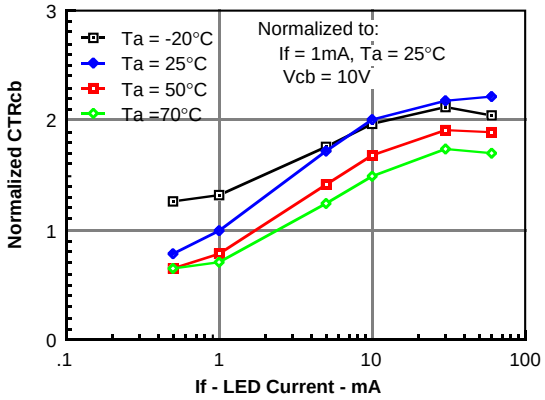


Figure 4. Normalized CTR_{CE} versus LED current

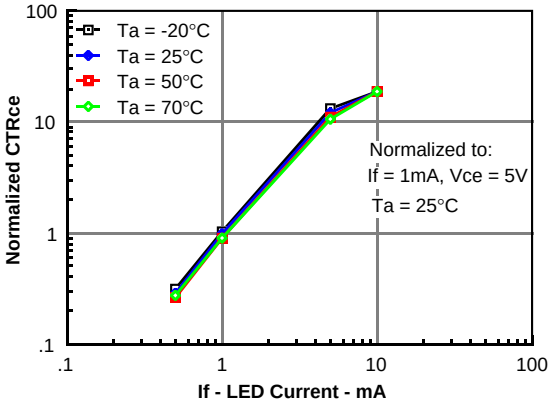


Figure 5. CTR_{CB} versus LED current

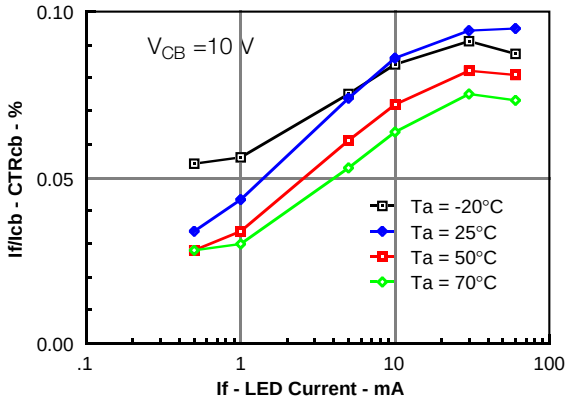


Figure 6. CTR versus LED current

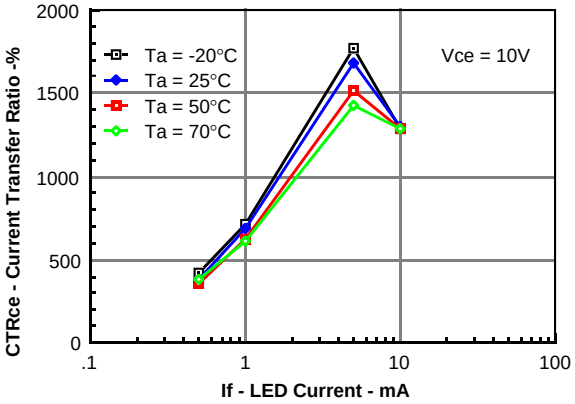


Figure 7. Collector current versus LED current

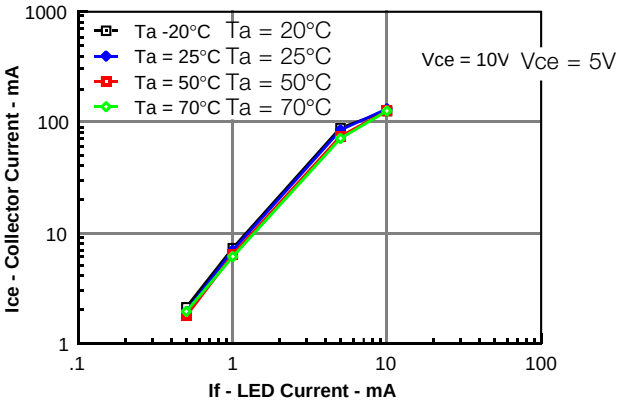


Figure 8. Photocurrent versus LED current

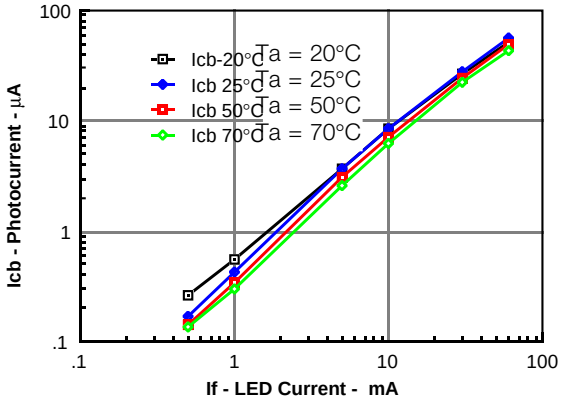


Figure 9. Normalized I_{CB} versus I_F

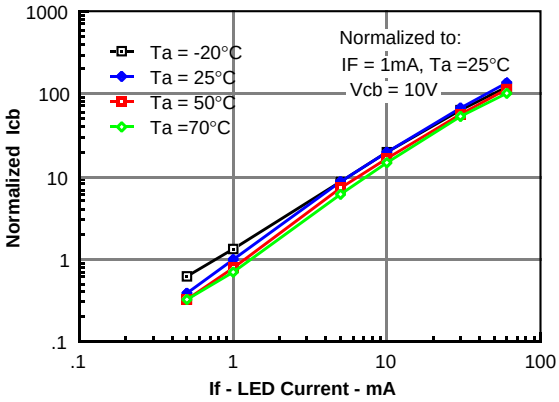


Figure 10. Switching Timing

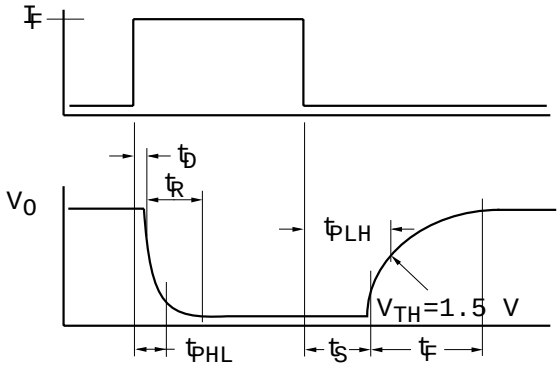


Figure 11. Switching schematic